

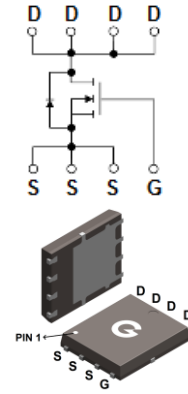
Features

- Advanced Shielded-Gate Trench technology
- Ultra-low on-resistance
- Low gate-charge
- HBM: JESD22-A114-B: 1A

HF

Mechanical Data

- Case: PDFN5×6-8L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



PDFN5×6-8L

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL035N04T-5DL8	PDFN5×6-8L	5000 pcs / Tape & Reel	035N04T

Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	40	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (T _C = 25°C, Silicon Limited)	I _D	118	A
Continuous Drain Current (T _C = 25°C, Package Limited)		100	A
Continuous Drain Current (T _C = 100°C)		75	A
Continuous Drain Current (T _A = 25°C) *1		23	A
Continuous Drain Current (T _A = 100°C) *1		15	A
Pulsed Drain Current (t _p ≤ 10μs, T _C = 25°C)	I _{DM}	400	A
Single Pulse Avalanche Energy *3	E _{AS}	100	mJ
Power Dissipation (T _C = 25°C)	P _D	78	W
Operating Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	R _{θJC}	-	1.3	1.6	°C/W
Thermal Resistance Junction-to-Air *1	R _{θJA}	-	30	40	°C/W

Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 40V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *2	V _{GS} = 10V, I _D = 20A	-	2.8	3.5	mΩ
		V _{GS} = 4.5V, I _D = 20A	-	4.0	5.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1	1.7	2.5	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	4.7	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V	-	1685	-	pF
C _{OSS}	Output Capacitance	V _{DS} = 20V	-	647	-	
C _{RSS}	Reverse Transfer Capacitance	f = 1.0MHz	-	9	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time	V _{DD} = 30V	-	14	-	ns
t _r	Turn-on Rise Time	V _{GS} = 15V	-	62	-	
t _{d(OFF)}	Turn-Off Delay Time	I _D = 20A	-	50	-	
t _f	Turn-Off Fall Time	R _G = 3.3Ω	-	27	-	
Q _G	Total Gate-Charge	V _{DD} = 20V	-	27	-	nC
Q _{GS}	Gate to Source Charge	V _{GS} = 10V	-	4.5	-	
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 20A	-	5	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *2	I _S = 20A, V _{GS} = 0V	-	0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _S = 20A, V _{GS} = 0V	-	65	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt = 100A/μs	-	66	-	nC

Notes:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 20V, V_{GS} = 10V, L = 0.5mH$

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

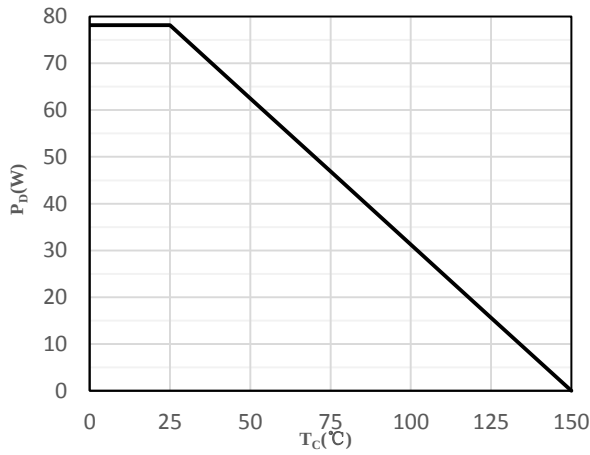


Fig 1 Power Dissipation

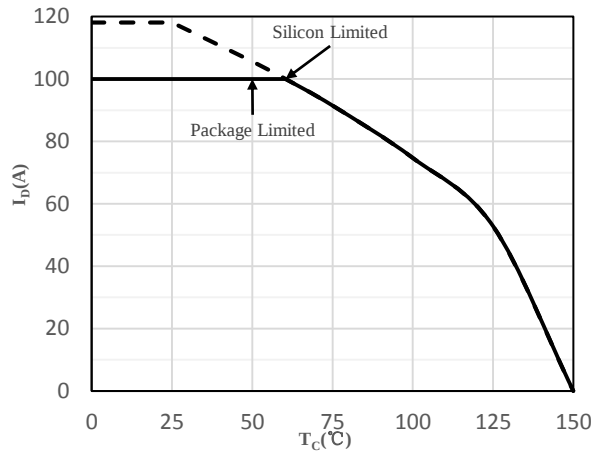


Fig 2 Drain Current

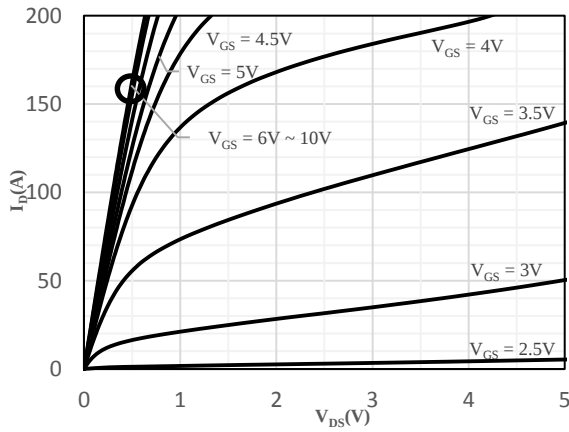


Fig 3 Typical Output Characteristics

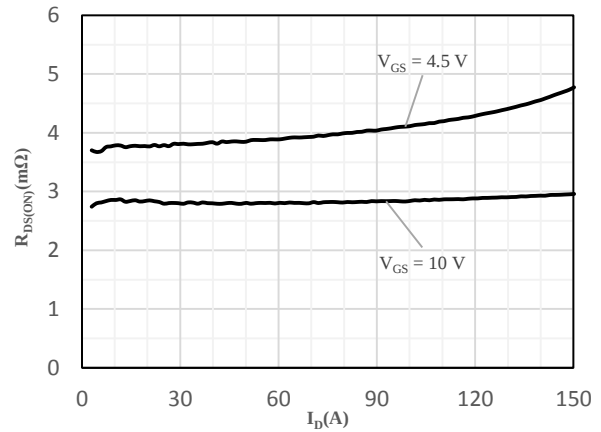


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

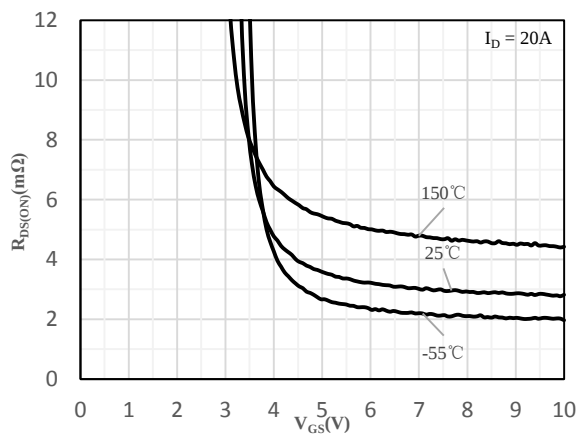


Fig 5 On-Resistance vs. Gate-Source Voltage

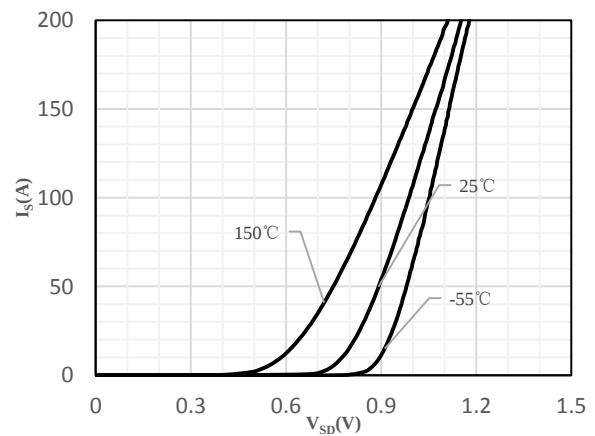


Fig 6 Body-Diode Characteristics

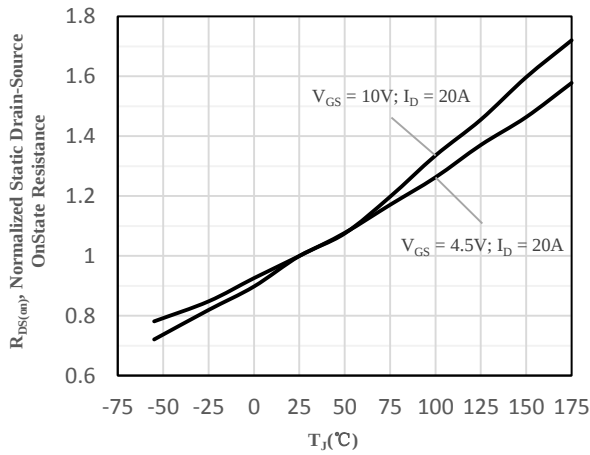


Fig 7 Normalized On-Resistance vs. Junction Temperature

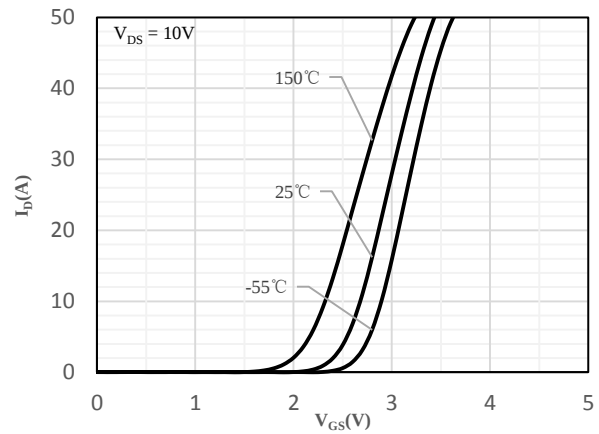


Fig 8 Transfer Characteristics

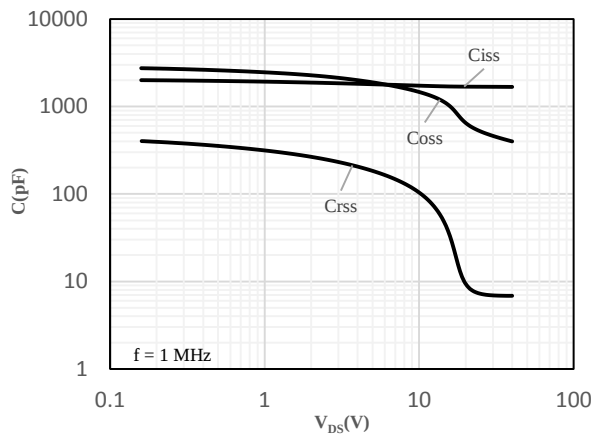


Fig 9 Capacitance Characteristics

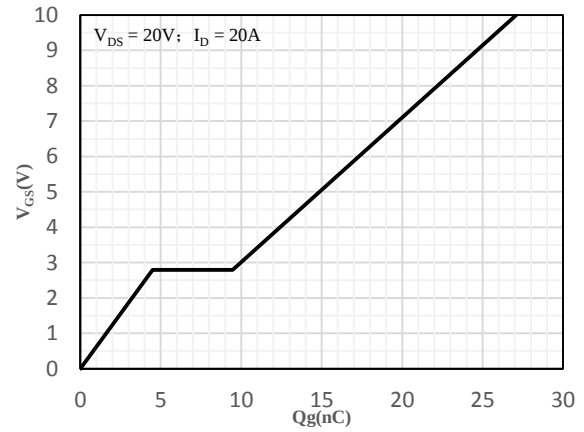


Fig 10 Gate-Charge Characteristics

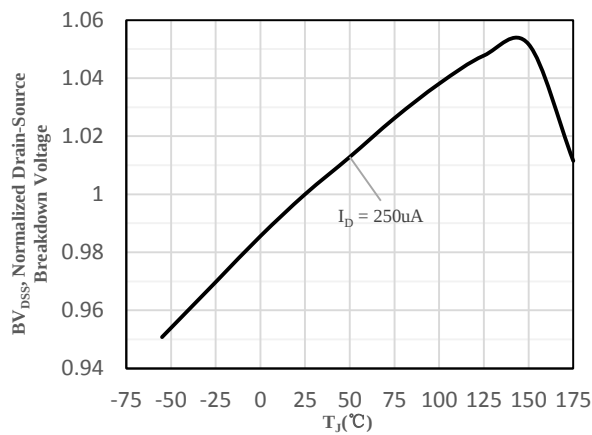


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

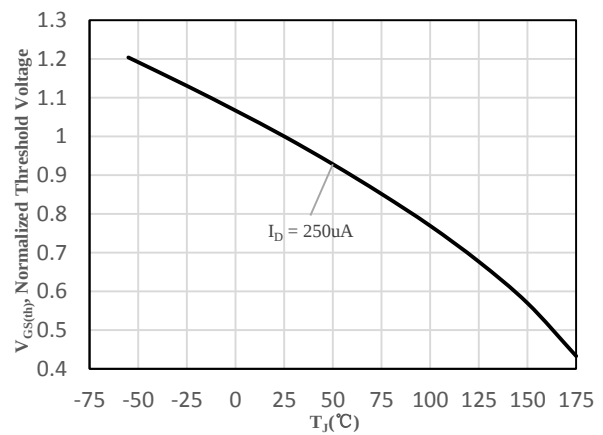
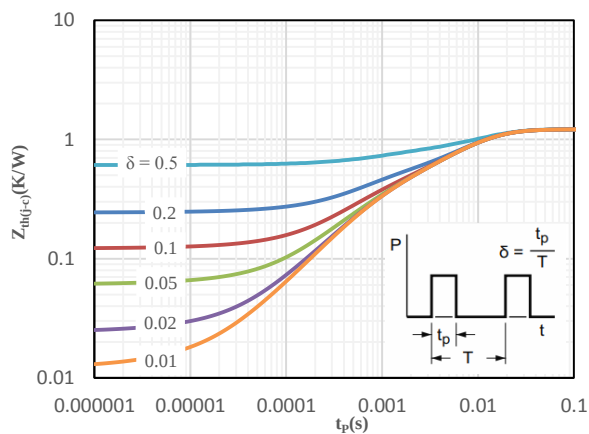
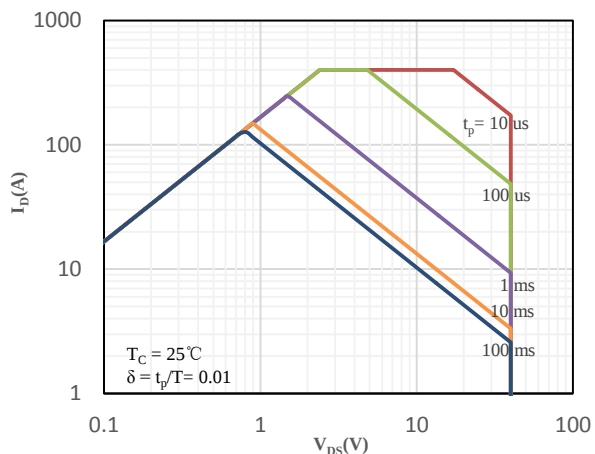
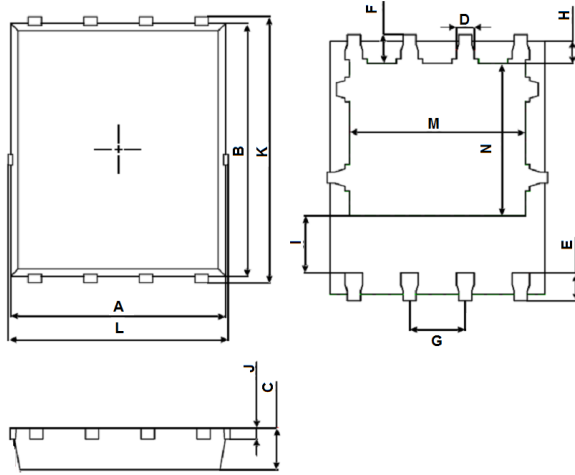


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature



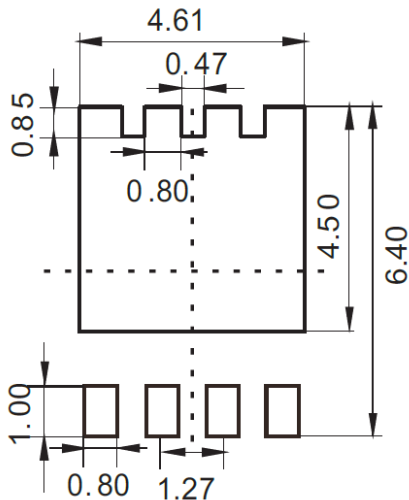
Package Outline Dimensions (Unit: mm)



PDFN5×6-8L		
Dimension	Min.	Max.
A	4.824	4.976
B	5.674	5.826
C	0.900	1.000
D	0.350	0.450
E	0.559	0.711
F	0.574	0.726
G	1.250	1.290
H	0.424	0.576
I	1.190	1.390
J	0.154	0.354
K	5.974	6.126
L	4.944	5.096
M	3.910	4.110
N	3.375	3.575

Mounting Pad Layout (Unit: mm)

PDFN5×6-8L



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